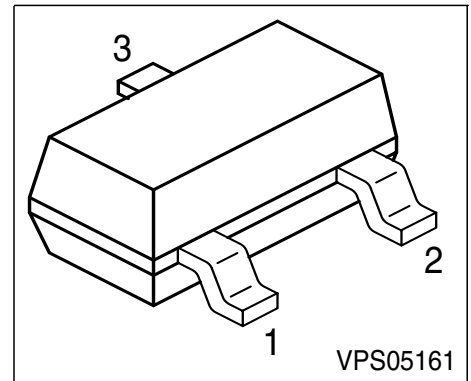


PNP Silicon AF Transistors

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 Hz and 15 kHz
- Complementary types: BC846, BC847, BC848
BC849, BC850 (NPN)



Type	Marking	Pin Configuration			Package
BC856A	3As	1 = B	2 = E	3 = C	SOT23
BC856B	3Bs	1 = B	2 = E	3 = C	SOT23
BC857A	3Es	1 = B	2 = E	3 = C	SOT23
BC857B	3Fs	1 = B	2 = E	3 = C	SOT23
BC857C	3Gs	1 = B	2 = E	3 = C	SOT23
BC858A	3Js	1 = B	2 = E	3 = C	SOT23
BC858B	3Ks	1 = B	2 = E	3 = C	SOT23
BC858C	3Ls	1 = B	2 = E	3 = C	SOT23
BC859A	4As	1 = B	2 = E	3 = C	SOT23
BC859B	4Bs	1 = B	2 = E	3 = C	SOT23
BC859C	4Cs	1 = B	2 = E	3 = C	SOT23
BC860B	4Fs	1 = B	2 = E	3 = C	SOT23
BC860C	4Gs	1 = B	2 = E	3 = C	SOT23

Maximum Ratings

Parameter	Symbol	BC856	BC857 BC860	BC858 BC859	Unit
Collector-emitter voltage	V_{CEO}	65	45	30	V
Collector-base voltage	V_{CBO}	80	50	30	
Collector-emitter voltage	V_{CES}	80	50	30	
Emitter-base voltage	V_{EBO}	5	5	5	
DC collector current	I_C	100			mA
Peak collector current	I_{CM}	200			mA
Peak base current	I_{BM}	200			
Peak emitter current	I_{EM}	200			
Total power dissipation, $T_S = 71\text{ °C}$	P_{tot}	330			mW
Junction temperature	T_j	150			°C
Storage temperature	T_{sta}	-65 ... 150			

Thermal Resistance

Junction - soldering point ¹⁾	R_{thJS}	≤240	K/W
--	------------	------	-----

Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 10\text{ mA}$, $I_B = 0$	BC856	$V_{(BR)CEO}$	65	-	-	V
	BC857/860		45	-	-	
	BC858/859		30	-	-	
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$	BC856	$V_{(BR)CBO}$	80	-	-	
	BC857/860		50	-	-	
	BC858/859		30	-	-	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

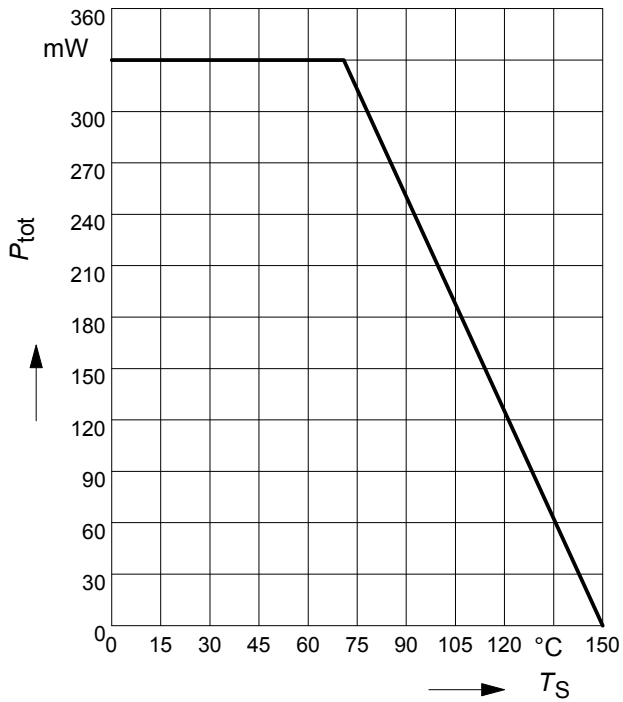
Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
DC Characteristics						
Collector-emitter breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $V_{BE} = 0$ BC856 BC857/860 BC858/859	$V_{(BR)CES}$	80 50 30	- - -	- - -	V	
Emitter-base breakdown voltage $I_E = 1\text{ }\mu\text{A}$, $I_C = 0$	$V_{(BR)EBO}$	5	-	-		
Collector cutoff current $V_{CB} = 30\text{ V}$, $I_E = 0$	I_{CBO}	-	-	15	nA	
Collector cutoff current $V_{CB} = 30\text{ V}$, $I_E = 0$, $T_A = 150\text{ }^\circ\text{C}$	I_{CBO}	-	-	5	μA	
DC current gain 1) $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$ h_{FE}-group A h_{FE}-group B h_{FE}-group C	h_{FE}	- - -	140 250 480	- - -	-	
DC current gain 1) $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$ h_{FE}-group A h_{FE}-group B h_{FE}-group C	h_{FE}	125 220 420	180 290 520	250 475 800		
Collector-emitter saturation voltage1) $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat}	- -	75 250	300 650		mV
Base-emitter saturation voltage 1) $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{BEsat}	- -	700 850	- -		
Base-emitter voltage 1) $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$	$V_{BE(ON)}$	600 -	650 -	750 820		

1) Pulse test: $t \leq 300\mu\text{s}$, $D = 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

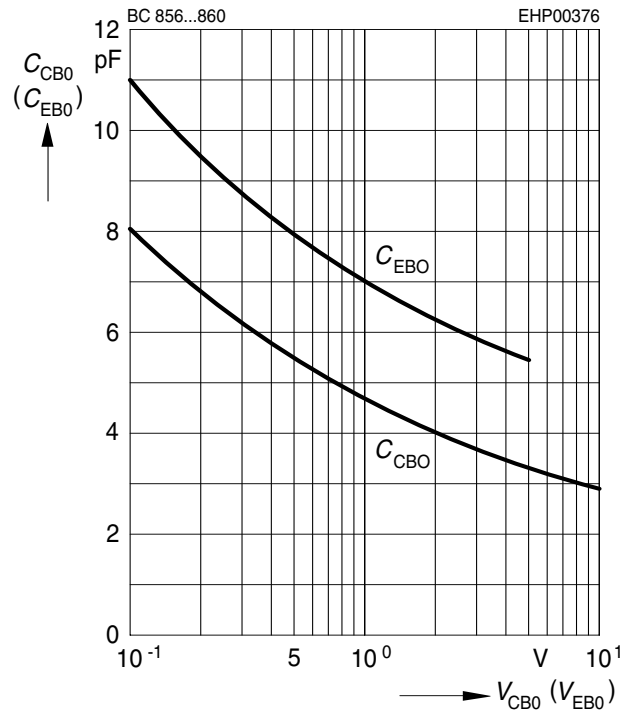
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 20\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 100\text{ MHz}$	f_T	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	3	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	8	-	
Short-circuit input impedance $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{11e}	-	2.7	-	kΩ
$h_{FE-gr.A}$		-	4.5	-	
$h_{FE-gr.B}$		-	8.7	-	
Open-circuit reverse voltage transf.ratio $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{12e}	-	1.5	-	10^{-4}
$h_{FE-gr.A}$		-	2	-	
$h_{FE-gr.B}$		-	3	-	
Short-circuit forward current transf.ratio $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{21e}	-	200	-	-
$h_{FE-gr.A}$		-	330	-	
$h_{FE-gr.B}$		-	600	-	
Open-circuit output admittance $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, $f = 1\text{ kHz}$	h_{22e}	-	18	-	μS
$h_{FE-gr.A}$		-	30	-	
$h_{FE-gr.B}$		-	60	-	
Noise figure $I_C = 0.2\text{ mA}$, $V_{CE} = 5\text{ V}$, $R_S = 2\text{ k}\Omega$, $f = 1\text{ kHz}$, $\Delta f = 200\text{ Hz}$	F	-	1	4	dB
Equivalent noise voltage $I_C = 200\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, $R_S = 2\text{ k}\Omega$, $f = 10 \dots 50\text{ Hz}$	V_n	-	-	0.11	μV

Total power dissipation $P_{\text{tot}} = f(T_S)$



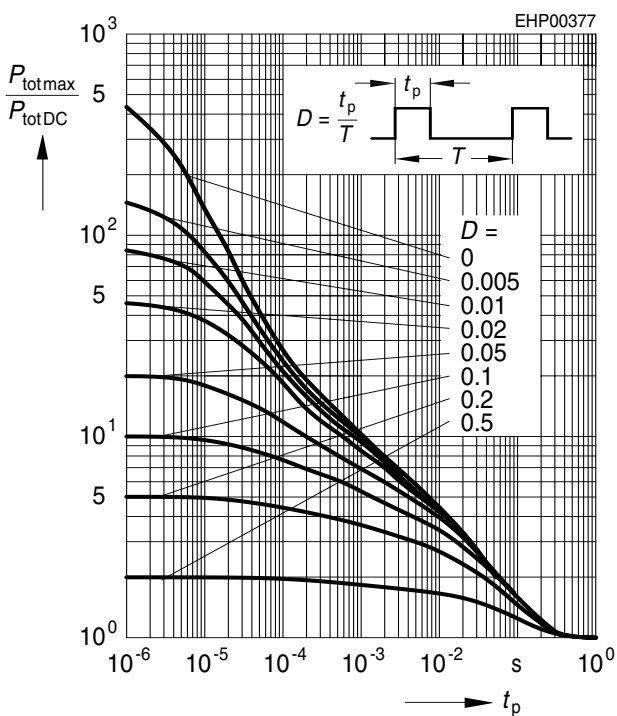
Collector-base capacitance $C_{CB} = f(V_{CB0})$

Emitter-base capacitance $C_{EB} = f(V_{EB0})$



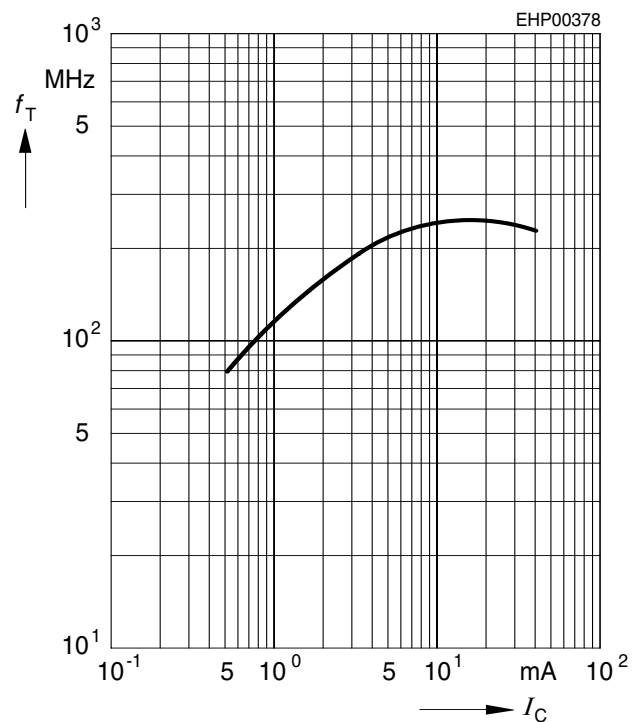
Permissible pulse load

$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$



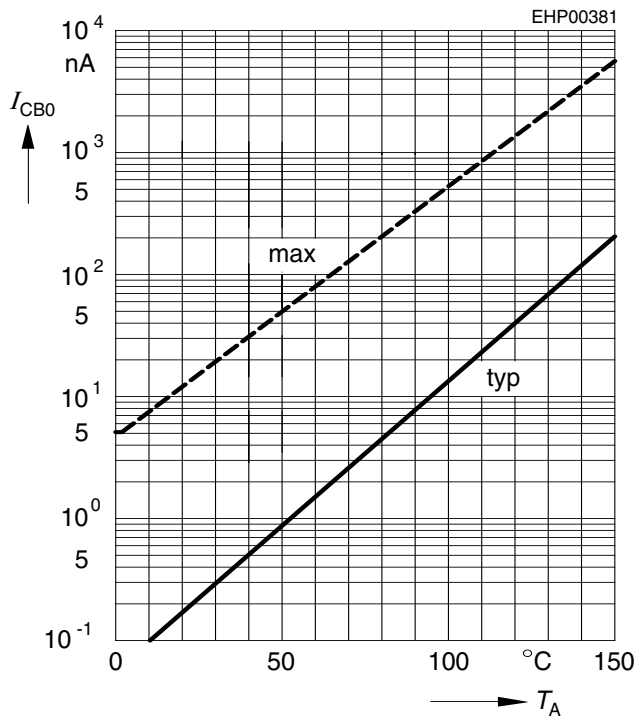
Transition frequency $f_T = f(I_C)$

$V_{CE} = 5V$



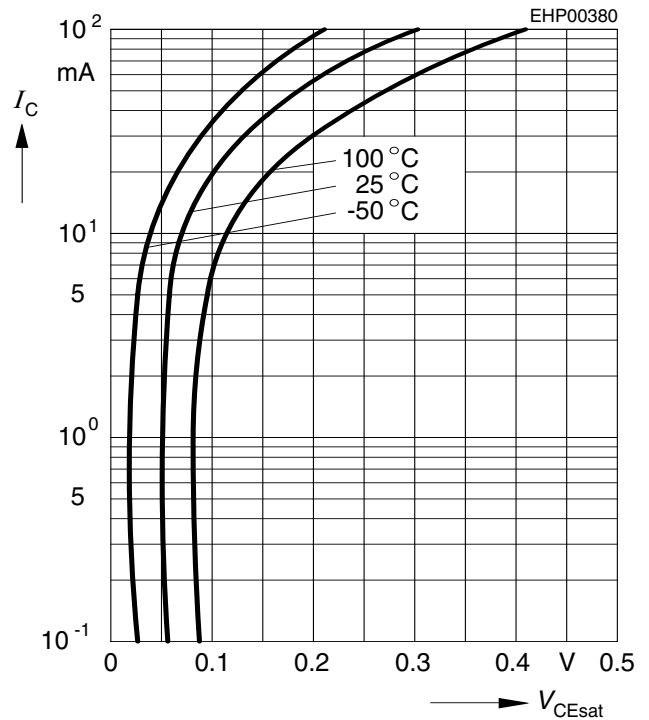
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CB} = 30V$



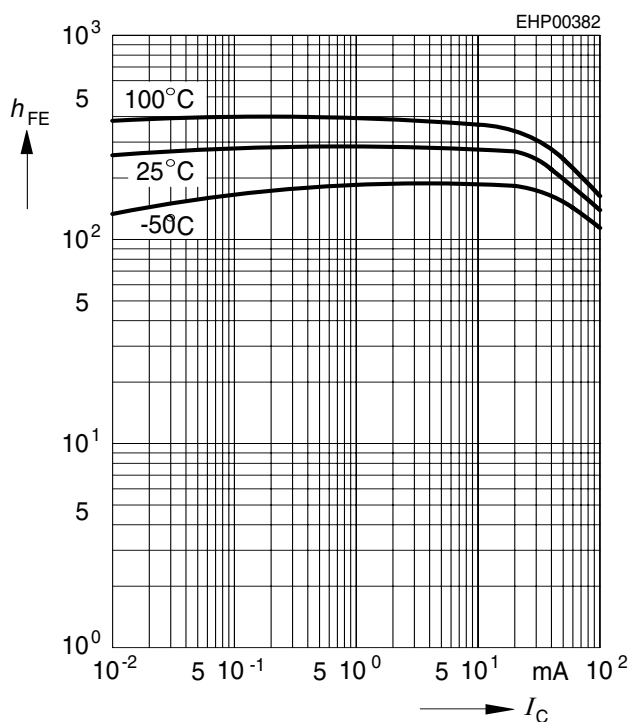
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 20$



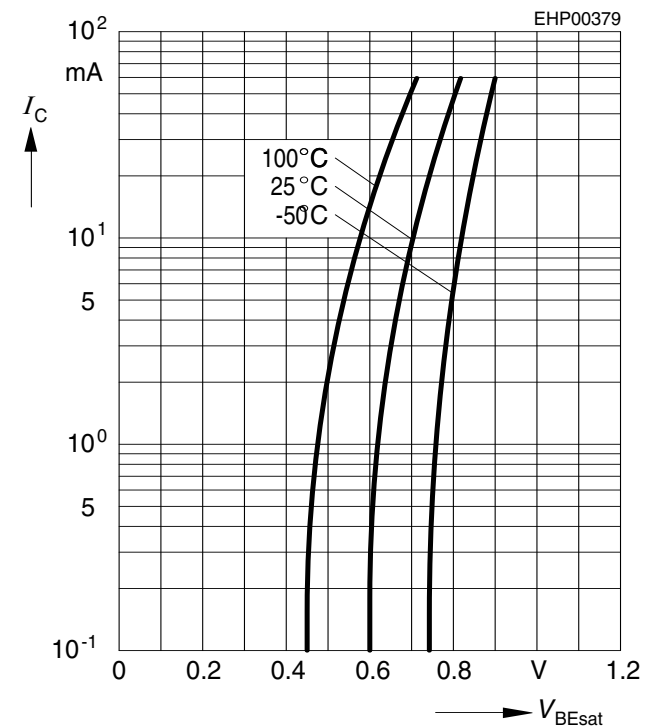
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$



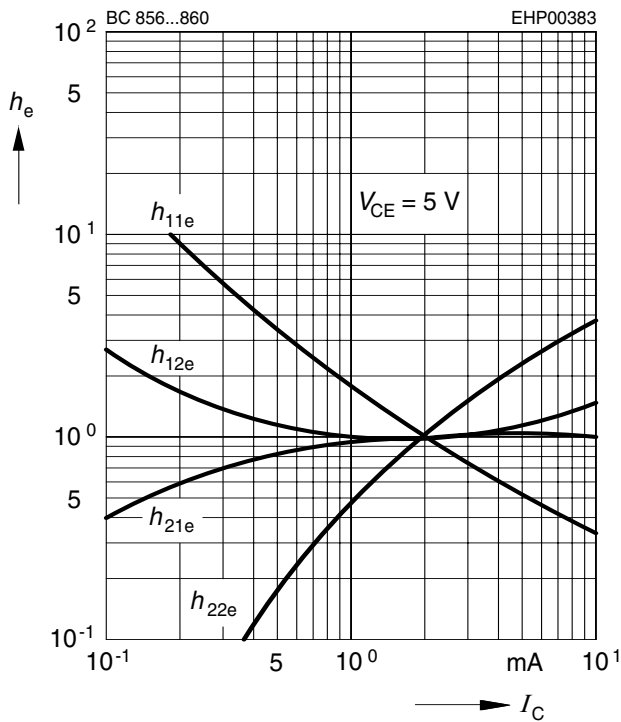
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 20$



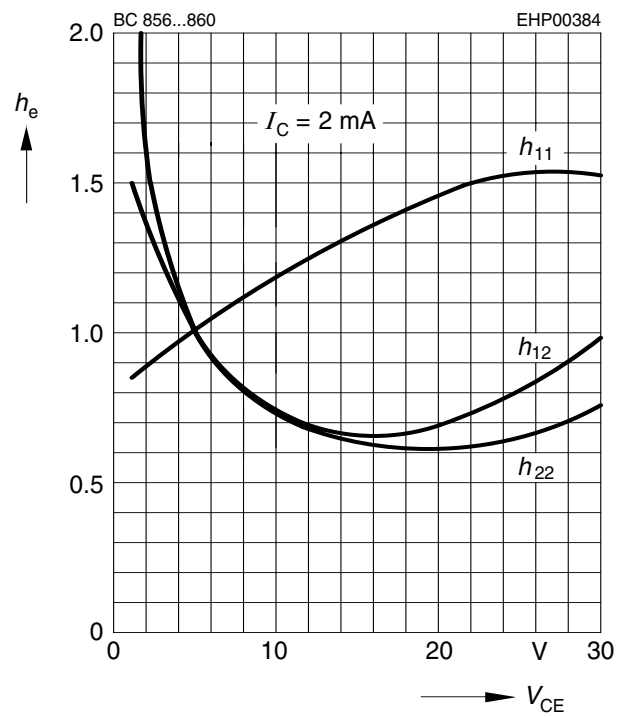
h parameter $h_e = f(I_C)$ normalized

$V_{CE} = 5V$



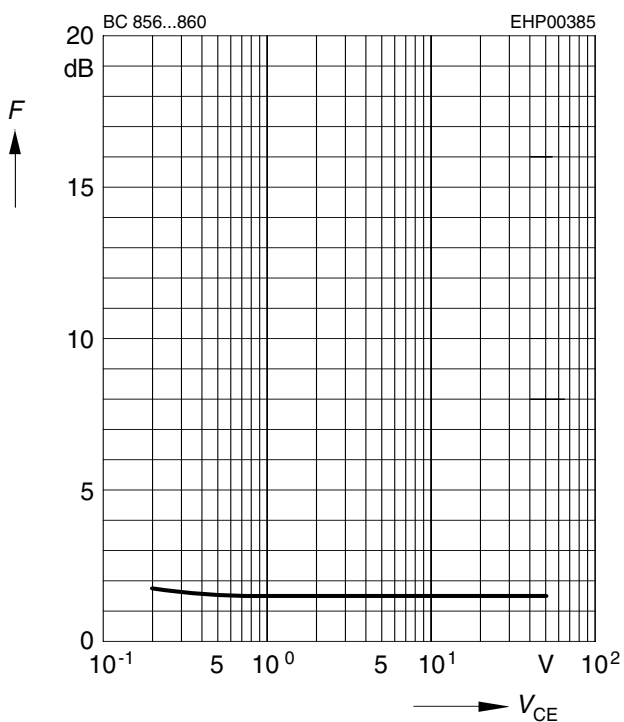
h parameter $h_e = f(V_{CE})$ normalized

$I_C = 2mA$



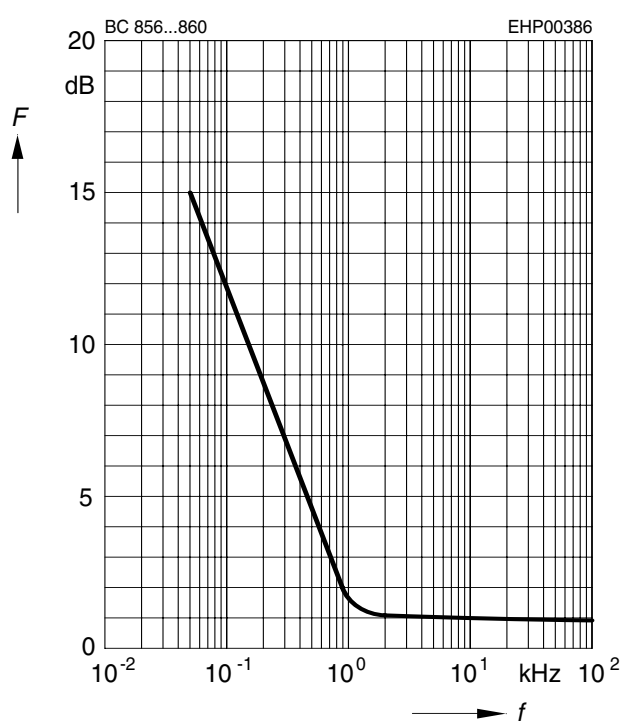
Noise figure $F = f(V_{CE})$

$I_C = 0.2mA$, $R_S = 2k\Omega$, $f = 1kHz$



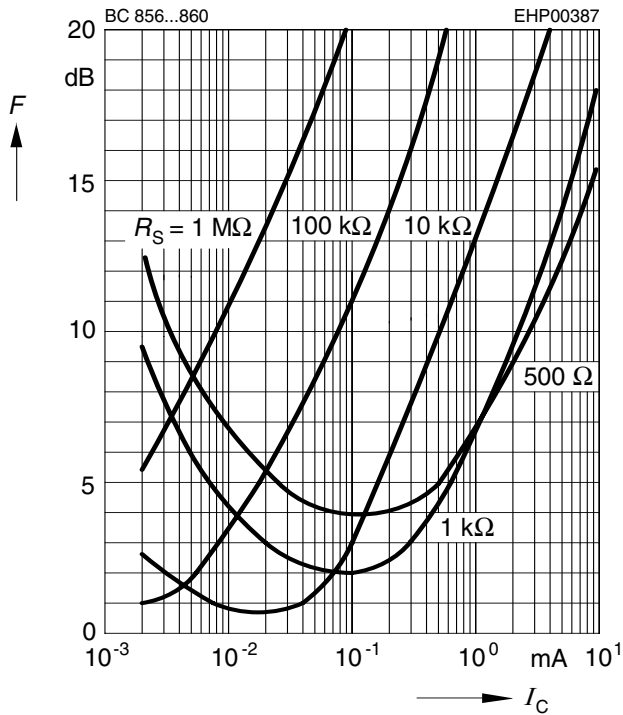
Noise figure $F = f(f)$

$I_C = 0.2mA$, $V_{CE} = 5V$, $R_S = 2k\Omega$



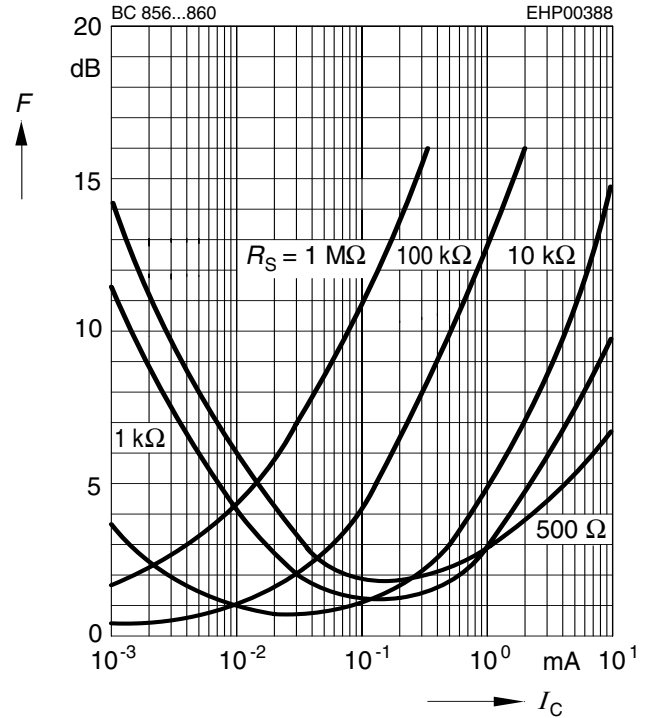
Noise figure $F = f(I_C)$

$V_{CE} = 5V, f = 120Hz$



Noise figure $F = f(I_C)$

$V_{CE} = 5V, f = 1kHz$



Noise figure $F = f(I_C)$

$V_{CE} = 5V, f = 10kHz$

